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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/024,958		
		Filing Date	DECEMBER 18, 2001		
		First Named Inventor	BUIE, ET AL.		
		Group Art Unit	1765		
		Examiner Name	KEN-CHAN CHEN		
		Attorney Docket Number	AMAT/4213.P1/MASK/MASK-ETCH/ARNOLD S		
Sheet	1	of	1	Submission Date	April 12, 2004

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
K-CC	A1	PCT Search Report for PCT/US03/11549, dated February 19, 2004 (AMAT/6991.PC)	—
K-CC	A2	KWON, ET AL., "Loading Effect Parameters at Dry Etcher System and Their Analysis at Mask-to-Mask Loading and Within-Mask Loading" Proceedings of SPIE, Vol. 4562 (2002) pp. 79-87.	—
K-CC	A3	FUJISAWA, ET AL. "Evaluation of NLD Mask Dry Etching System" SPIE Symposium on Photomask and X-Ray Technology VI, Yokohama, JAPAN, September (1999) Vol. 3748 pp. 147-152.	—
K-CC	A4	RUHL, ET AL. "Chrome Dry Etch Process Characterization Using Surface Nano Profiling" Proceedings of SPIE, Vol. 4186 (2001) pp. 97-107.	—
K-CC	A5	AOYAMA, ET AL. "Advanced Cr Dry Etching Process" SPIE Symposium on Photomask and X-Ray Technology VI, Yokohama, JAPAN, September (1999) SPIE, Vol. 3748 pp. 137-146.	—

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K-CC. [Signature]

Date Considered

3-21-05

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